

GSM4924W

40V N-Channel Enhancement Mode MOSFET

Product Description

GSM4924W, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

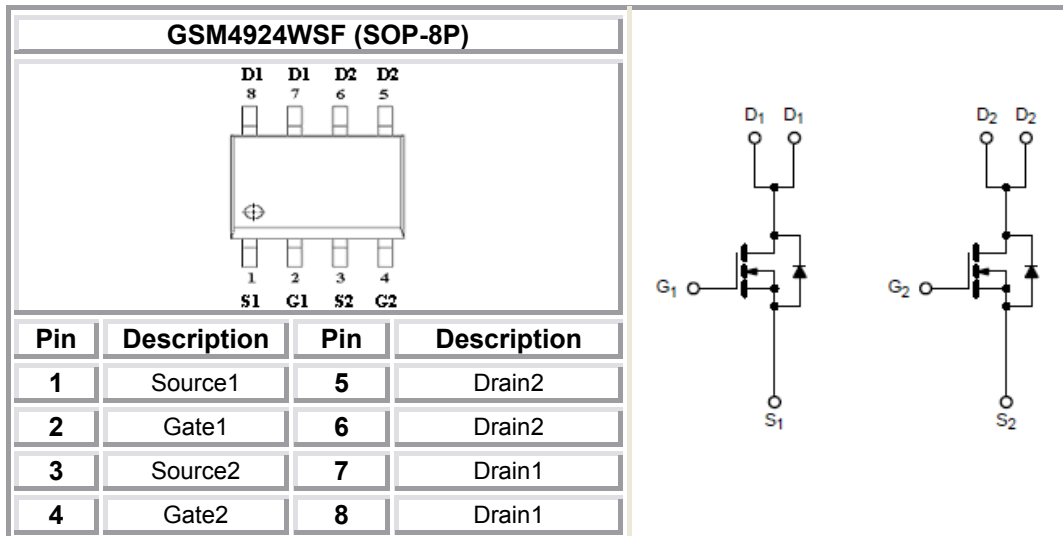
Features

- 40V/8A, $R_{DS(ON)}=22m\Omega@V_{GS}=10V$
- 40V/6A, $R_{DS(ON)}=28m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- SOP-8P package design
- RoHS Compliant, 100%Pb & Halogen Free

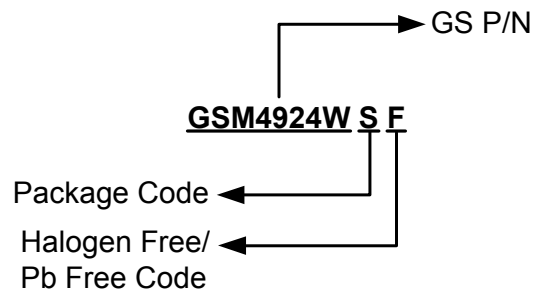
Applications

- Motor and Load Control
- AD/DC Inverter Systems.
- Power Management in White LED System

Packages & Pin Assignments

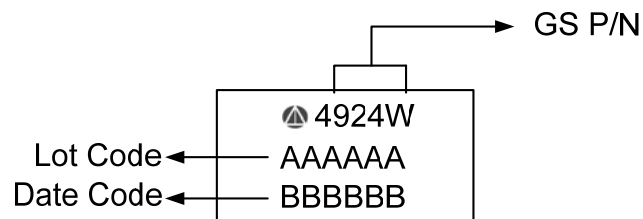


Ordering Information



Part Number	Package	Quantity Reel
GSM4924WSF	SOP-8P	2500 PCS

Marking Information



Absolute Maximum Ratings

($T_A=25^\circ\text{C}$ unless otherwise noted)

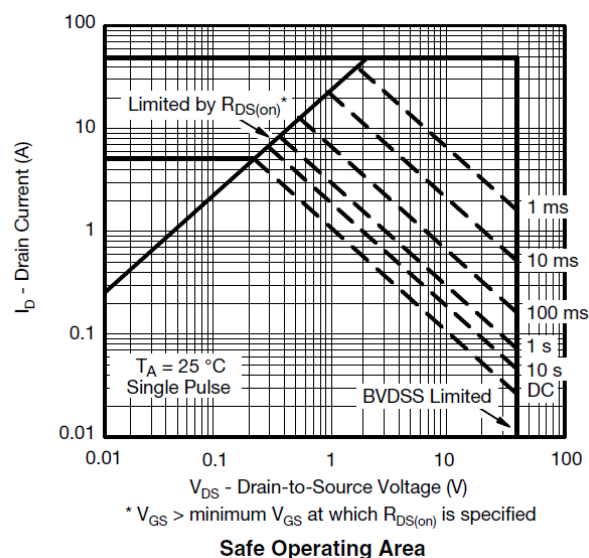
Symbol	Parameter	Typical	Unit	
V_{DSS}	Drain-Source Voltage	40	V	
V_{GSS}	Gate -Source Voltage	± 20	V	
I_D	Continuous Drain Current($T_J=150^\circ\text{C}$)	$T_A=25^\circ\text{C}$	8	A
		$T_A=70^\circ\text{C}$	6	
I_{DM}	Pulsed Drain Current	30	A	
I_S	Continuous Source Current(Diode Conduction)	1.5	A	
P_D	Power Dissipation	$T_A=25^\circ\text{C}$	2.8	W
		$T_A=70^\circ\text{C}$	1.8	
T_J	Operating Junction Temperature	150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-55/150	$^\circ\text{C}$	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	$^\circ\text{C}/\text{W}$	

Electrical Characteristics

($T_A=25^\circ\text{C}$ unless otherwise noted)

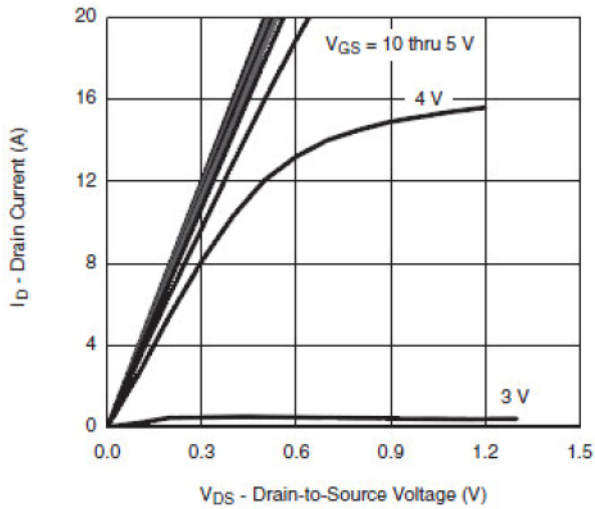
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.5		3.0	V
I_{GSS}	Gate Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=32V, V_{GS}=0V$			1	uA
		$V_{DS}=32V, V_{GS}=0V, T_J=85^\circ\text{C}$			10	
$I_{D(on)}$	On-State Drain Current	$V_{DS}\geq 5V, V_{GS}=10V$	20			A
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V, I_D=8A$		15	22	m Ω
		$V_{GS}=4.5V, I_D=6A$		20	28	
g_{FS}	Forward Transconductance	$V_{DS}=15V, I_D=5.0A$		25		S
V_{SD}	Diode Forward Voltage	$I_S=2A, V_{GS}=0V$		0.85	1.2	V
Dynamic						
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, f=1\text{MHz}$		850		pF
C_{oss}	Output Capacitance			110		
C_{rss}	Reverse Transfer Capacitance			75		
Q_g	Total Gate Charge	$V_{DS}=20V, V_{GS}=4.5V, I_D=5A$		10	14	nC
Q_{gs}	Gate-Source Charge			2.8		
Q_{gd}	Gate-Drain Charge			3.2		
$t_{d(on)}$	Turn-On Time	$V_{DD}=20V, R_L=4\Omega, I_D=5.0A, V_{GEN}=10V, R_G=1\Omega$		6	12	ns
t_r				10	20	
$t_{d(off)}$	Turn-Off Time			20	36	
t_f				6	12	

Typical Performance Characteristics

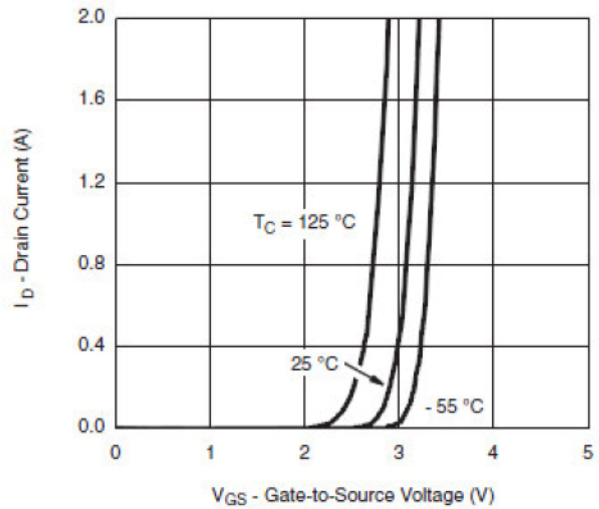


Typical Performance Characteristics (continue)

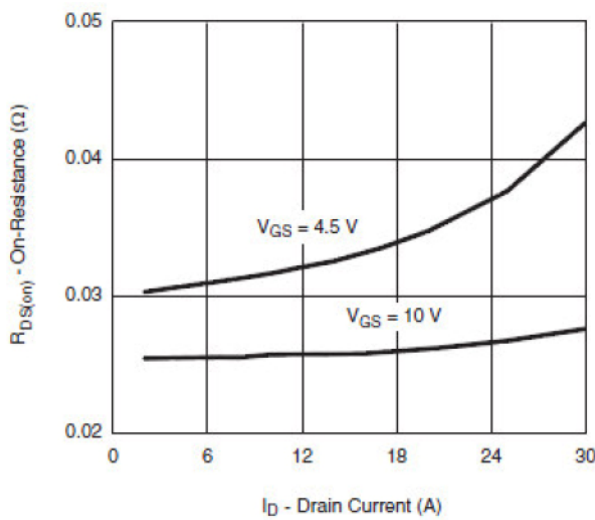
Output Characteristics



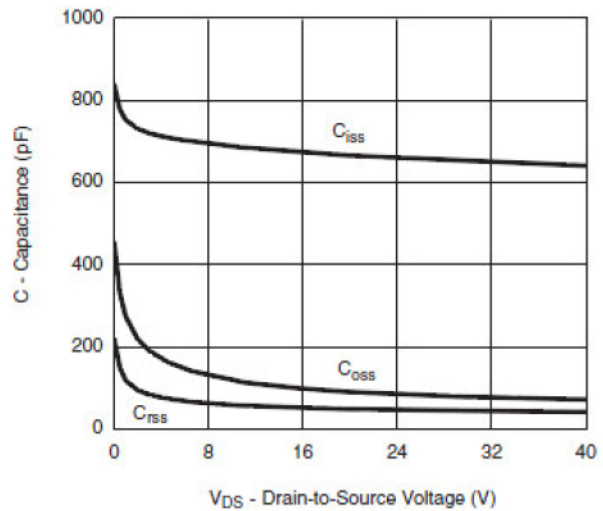
Transfer Characteristics



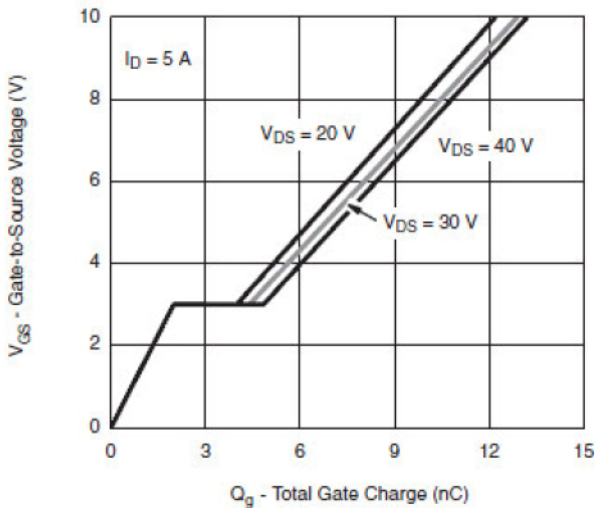
On-Resistance vs. Drain Current and Gate Voltage



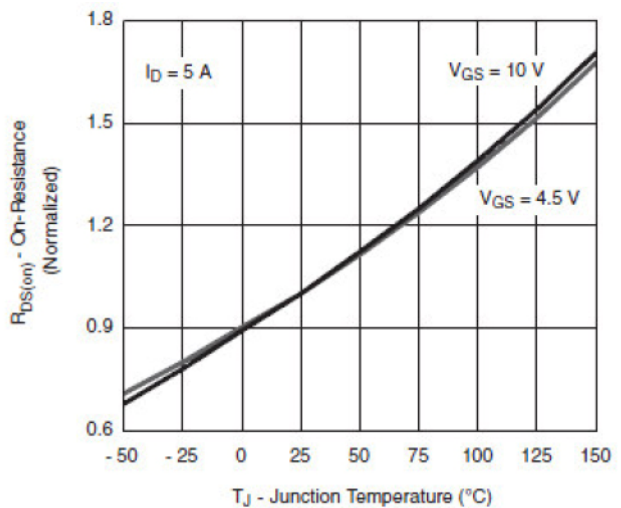
Capacitance



Gate Charge

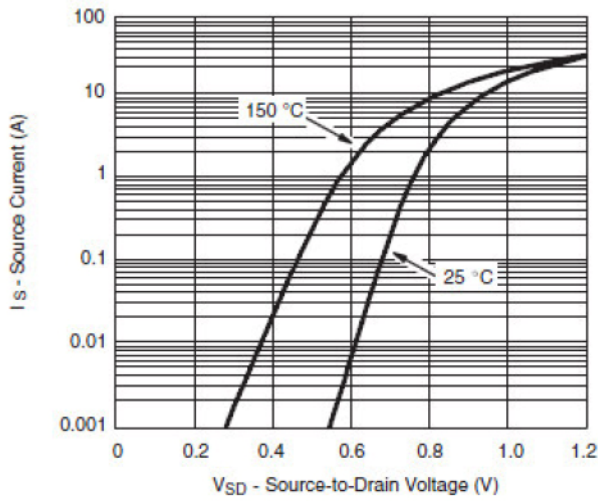


On-Resistance vs. Junction Temperature

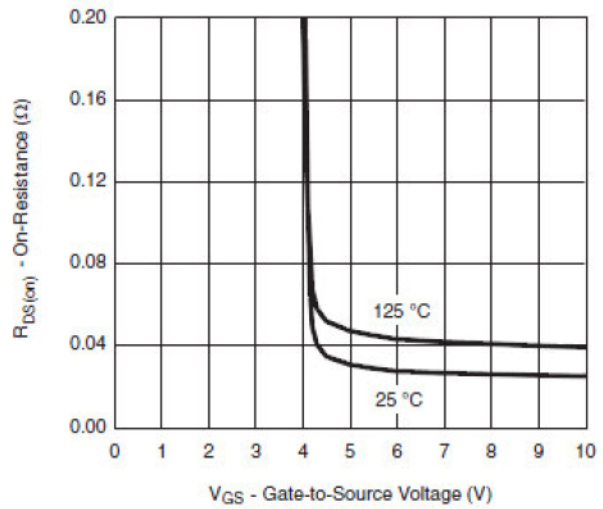


Typical Performance Characteristics (continue)

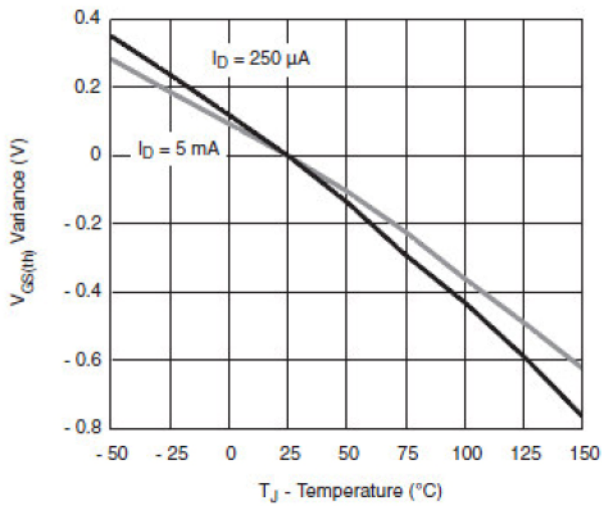
Source-Drain Diode Forward Voltage



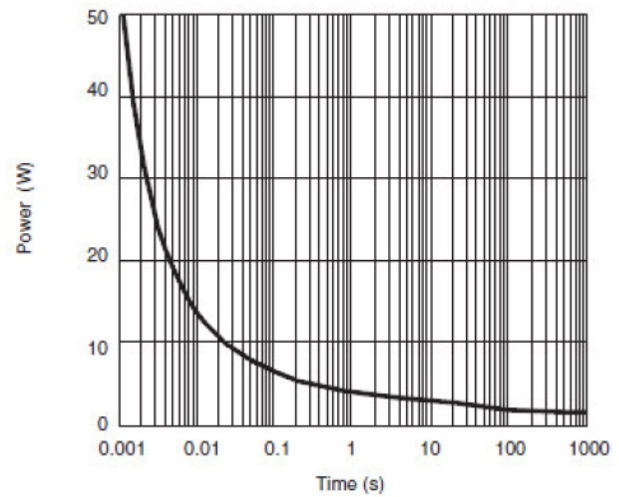
On-Resistance vs. Gate-to-Source Voltage



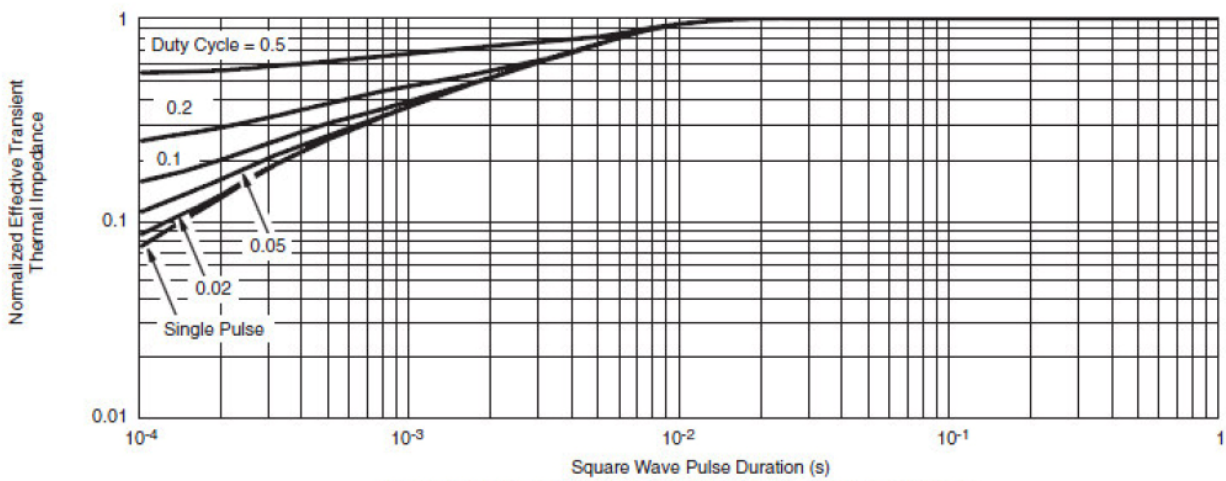
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

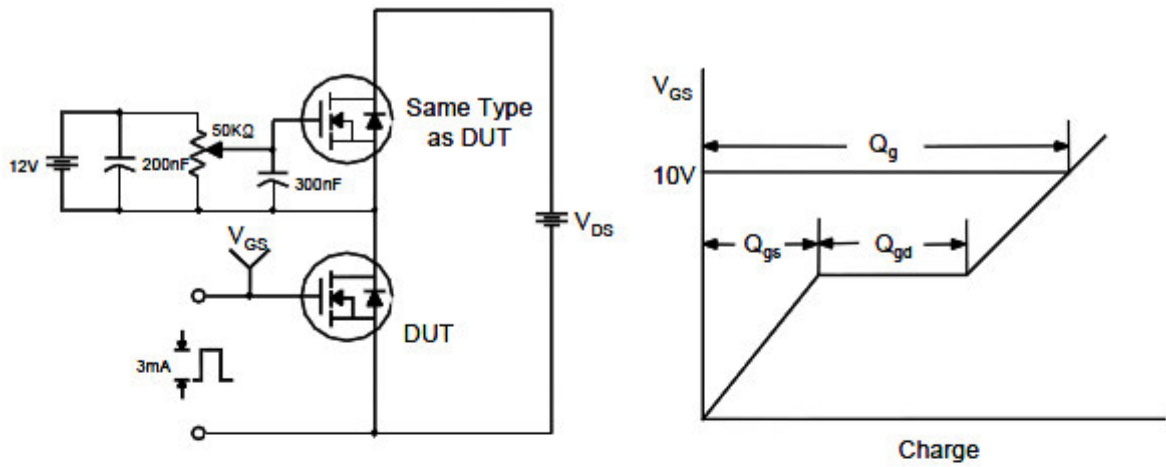


Normalized Thermal Transient Impedance, Junction-to-Case

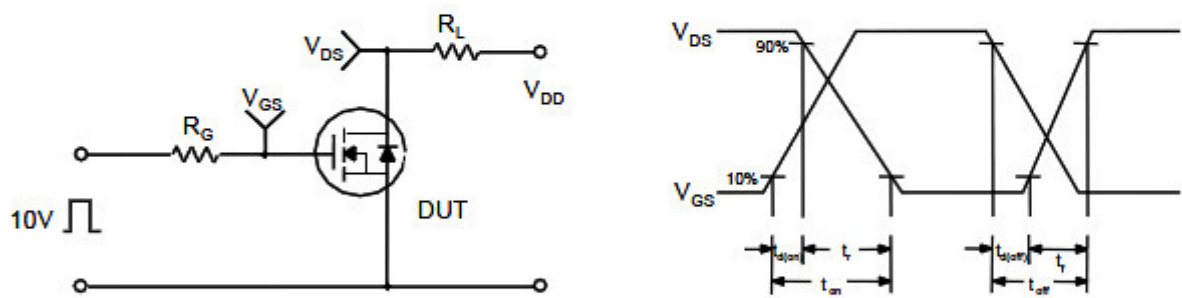


Typical Characteristics

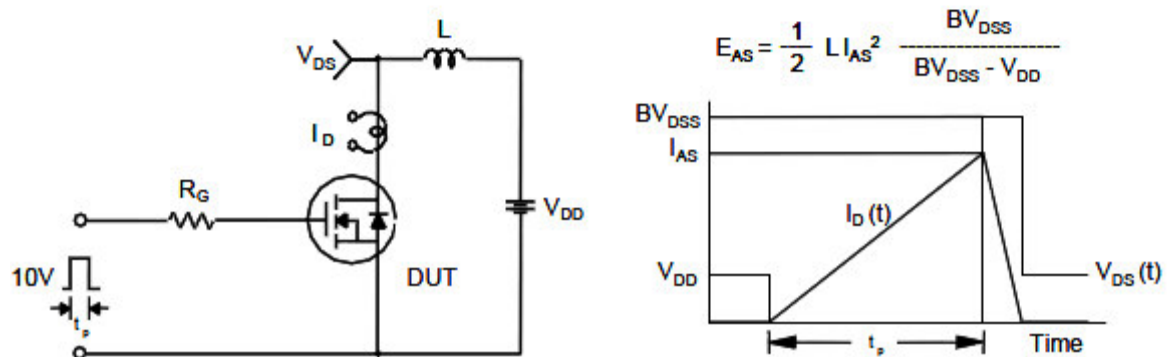
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

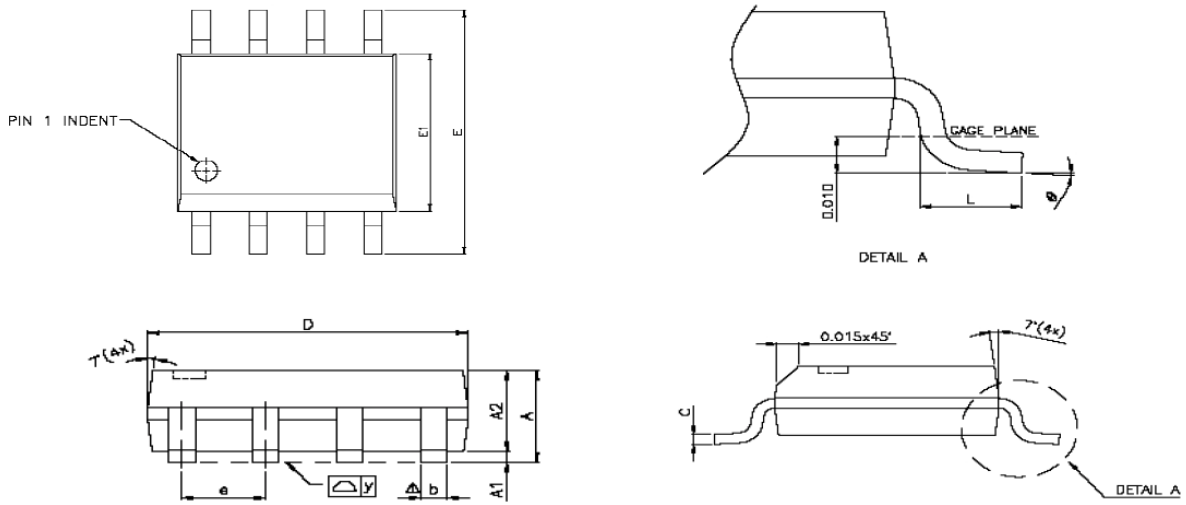


Unclamped Inductive Switching Test Circuit & Waveforms



Package Dimension

SOP-8P







Dimensions

Symbol	Millimeters			Inches		
	Min	Nom	Max	Min	Nom	Max
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	-	0.25	0.004	-	0.010
A2	-	1.45	-	-	0.057	-
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	-	1.27	-	-	0.050	-
L	0.38	0.71	1.27	0.015	0.028	0.050
Δy	-	-	0.076	-	-	0.003
θ	0°	-	8°	0°	-	8°

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